



October 2013

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance:
 - $R_{DS(ON)} < 54m\Omega$ @ $V_{GS} = 10V$
 - $R_{DS(ON)}$ < 72m Ω @ V_{GS} = 4.5V
 - $R_{DS(ON)}$ < 115m Ω @ V_{GS} = 2.5V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

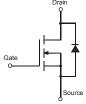
Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)

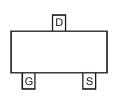
SOT-23







EQUIVALENT CIRCUIT



Pin Configuration

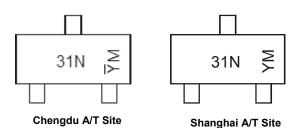
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3150L-7	SOT-23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/ products/packages.html

Marking Information



31N = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Y or \overline{Y} = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	2009	2010	20	11	2012	2013	2014	2015	20	16	2017	2018
Code	W	X	Y	′	Z	Α	В	С		D	Е	F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	±12	V
Drain Current (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	I _D	3.8 3.1	А
Drain Current (Note 5)	Pulsed	I _{DM}	15	A
Body-Diode Continuous Current (Note 5)		I _S	2.0	Α

Thermal Characteristics

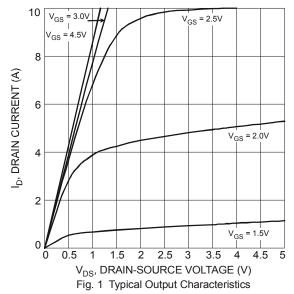
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_{D}	1.4	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{ hetaJA}$	90	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

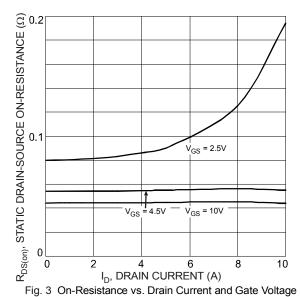
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 6)			ā.					
Drain-Source Breakdown Voltage	BV _{DSS}	30			V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	800	nA	$V_{DS} = 28V, V_{GS} = 0V$		
Gate-Body Leakage	I _{GSS}	_	_	±80	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 6)				±800		$V_{GS} = \pm 19V, V_{DS} = 0V$		
, ,	1,7	0.62	0.00	1.4	V	\\ -\\ \ \ \ - 250\		
Gate Threshold Voltage	V _{GS(th)}	0.62	0.92	1.4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$		
	1_	_	39	54	mΩ	$V_{GS} = 10V, I_D = 3.8A$		
Static Drain-Source On-Resistance	R _{DS (ON)}		52	72		$V_{GS} = 4.5V, I_D = 3.6A$		
			90	115		$V_{GS} = 2.5V, I_D = 3.1A$		
Forward Transconductance	Y _{fs}		3	_	S	$V_{DS} = 5V, I_{D} = 3.1A$		
Source-Drain Diode Forward Voltage	V_{SD}	_	_	1.16	V	$V_{GS} = 0V, I_{S} = 2.0A$		
DYNAMIC CHARACTERISTICS (Note 7)						_		
Gate Resistance	R_g	-	4.17	-	Ω	V_{DS} =0V, V_{GS} = 0V, f = 1MHz		
Total Gate Charge (10V)	Qg	-	8.2	-	nC	$V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V},$ $I_D = 3.8 \text{ A}$		
Total Gate Charge (4.5V)	Q_{α}	-	3.7	-	nC			
Gate-Source Charge	Qgs	-	0.7	-	nC	$V_{GS} = 4.5 \text{ V}, V_{DS} = 10 \text{ V},$		
Gate-Drain Charge	Q_{qd}	-	1.1	-	nC	I _D = 3.8 A		
Turn-On Delay Time	t _{D(on)}	-	1.14	-	ns			
Turn-On Rise Time	t _r	-	3.49	-	ns	V_{DD} = 15V, V_{GEN} = 10V, R_{GEN} = 6 Ω , R_{L} = 3.9 Ω		
Turn-Off Delay Time	t _{D(off)}	-	15.02	-	ns			
Turn-Off Fall Time	t _f	-	3.26	-	ns			
Input Capacitance	C _{iss}	_	305	_	pF	5)/ // 6)/		
Output Capacitance	Coss	_	74	_	pF	V _{DS} = 5V, V _{GS} = 0V - f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	_	48	_	pF	71 = 1.UIVIDZ		

- Device mounted on FR-4 PCB. t ≤5 sec.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.







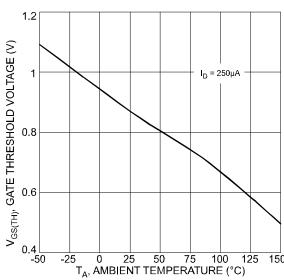
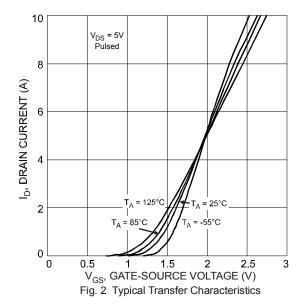
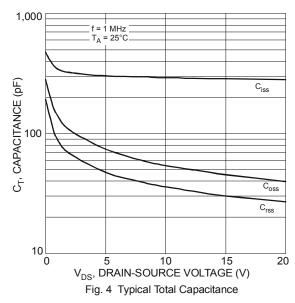


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature





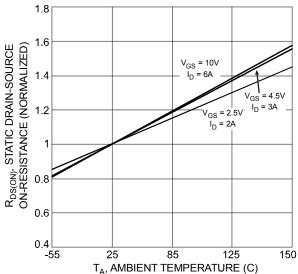
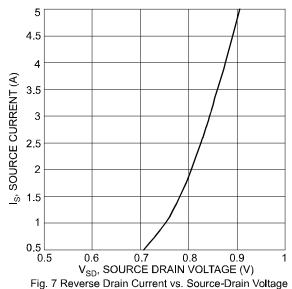


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature





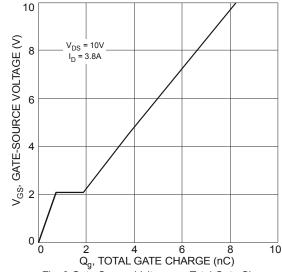
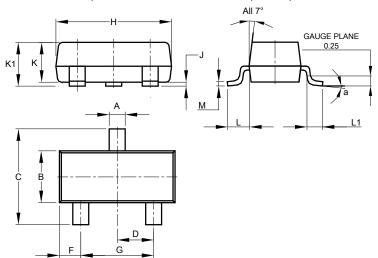


Fig. 8 Gate-Source Voltage vs. Total Gate Charge

Package Outline Dimensions

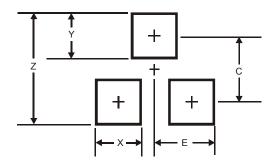
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Η	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
α	8°						
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	8.0
Υ	0.9
С	2.0
Е	1.35



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